

## High-Speed CMOS Logic Octal Three-State Bus Transceiver, Inverting

### Features

- Buffered Inputs
- Three-State Outputs
- Applications in Multiple-Data-Bus Architecture
- Fanout (Over Temperature Range)
  - Standard Outputs . . . . . 10 LSTTL Loads
  - Bus Driver Outputs . . . . . 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity:  $N_{IL} = 30\%$ ,  $N_{IH} = 30\%$  of  $V_{CC}$  at  $V_{CC} = 5V$
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility,  $V_{IL} = 0.8V$  (Max),  $V_{IH} = 2V$  (Min)
  - CMOS Input Compatibility,  $I_I \leq 1\mu A$  at  $V_{OL}$ ,  $V_{OH}$

### Description

The 'HC640 and 'HCT640 silicon-gate CMOS three-state bidirectional inverting and non-inverting buffers are intended for two-way asynchronous communication between data buses. They have high drive current outputs which enable high-speed operation when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuits, and have speeds comparable to low power Schottky TTL circuits. They can drive 15 LSTTL loads. The 'HC640 and 'HCT640 are inverting buffers.

The direction of data flow (A to B, B to A) is controlled by the DIR input.

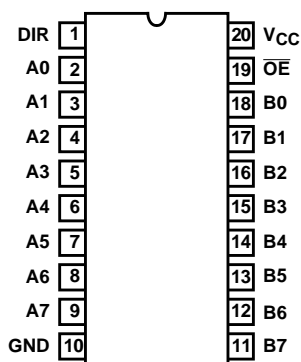
Outputs are enabled by a low on the Output Enable input ( $\overline{OE}$ ); a high  $\overline{OE}$  puts these devices in the high impedance mode.

### Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC640F3A	-55 to 125	20 Ld CERDIP
CD54HCT640F3A	-55 to 125	20 Ld CERDIP
CD74HC640E	-55 to 125	20 Ld PDIP
CD74HC640M	-55 to 125	20 Ld SOIC
CD74HCT640E	-55 to 125	20 Ld PDIP
CD74HCT640M	-55 to 125	20 Ld SOIC

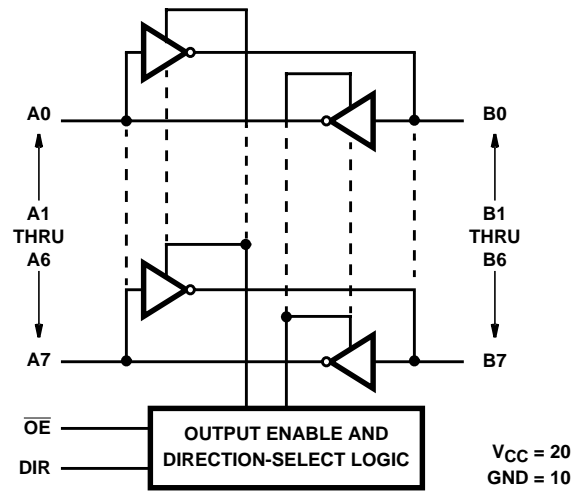
### Pinout

CD54HC640, CD54HCT640  
(CERDIP)  
CD74HC640, CD74HCT640  
(PDIP, SOIC)  
TOP VIEW



**CD54HC640, CD74HC640, CD54HCT640, CD74HCT640**

**Functional Diagram**



**TRUTH TABLE**

CONTROL INPUTS		DATA PORT STATUS	
$\overline{OE}$	DIR	A <sub>n</sub>	B <sub>n</sub>
L	L	$\overline{O}$	I
H	H	Z	Z
H	L	Z	Z
L	H	I	$\overline{O}$

To prevent excess currents in the High-Z modes all I/O terminals should be terminated with 1kΩ to 1MΩ resistors.

H = High Level

L = Low Level

I = Input

$\overline{O}$  = Output (Inversion of Input Level)

Z = High Impedance

# CD54HC640, CD74HC640, CD54HCT640, CD74HCT640

## Absolute Maximum Ratings

DC Supply Voltage, $V_{CC}$ .....	-0.5V to 7V
DC Input Diode Current, $I_{IK}$	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$ .....	$\pm 20mA$
DC Output Diode Current, $I_{OK}$	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$ .....	$\pm 20mA$
DC Drain Current, per Output, $I_O$	
For $-0.5V < V_O < V_{CC} + 0.5V$ .....	$\pm 35mA$
DC Output Source or Sink Current per Output Pin, $I_O$	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$ .....	$\pm 25mA$
DC $V_{CC}$ or Ground Current, $I_{CC}$ .....	$\pm 50mA$

## Thermal Information

Thermal Resistance (Typical, Note 1)	$\theta_{JA}$ ( $^{\circ}C/W$ )
E (PDIP) Package .....	69
M (SOIC) Package .....	58
Maximum Junction Temperature .....	$150^{\circ}C$
Maximum Storage Temperature Range .....	$-65^{\circ}C$ to $150^{\circ}C$
Maximum Lead Temperature (Soldering 10s) .....	$300^{\circ}C$ (SOIC - Lead Tips Only)

## Operating Conditions

Temperature Range, $T_A$ .....	$-55^{\circ}C$ to $125^{\circ}C$
Supply Voltage Range, $V_{CC}$	
HC Types .....	.2V to 6V
HCT Types .....	4.5V to 5.5V
DC Input or Output Voltage, $V_I, V_O$ .....	0V to $V_{CC}$
Input Rise and Fall Time	
2V .....	1000ns (Max)
4.5V .....	500ns (Max)
6V .....	400ns (Max)

*CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.*

### NOTE:

- The package thermal impedance is calculated in accordance with JESD 51-7.

## DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		$V_{CC}$ (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS	
		$V_I$ (V)	$I_O$ (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX		
<b>HC TYPES</b>													
High Level Input Voltage	$V_{IH}$	-	-	2	1.5	-	-	1.5	-	1.5	-	V	
				4.5	3.15	-	-	3.15	-	3.15	-	V	
				6	4.2	-	-	4.2	-	4.2	-	V	
Low Level Input Voltage	$V_{IL}$	-	-	2	-	-	0.5	-	0.5	-	0.5	V	
				4.5	-	-	1.35	-	1.35	-	1.35	V	
				6	-	-	1.8	-	1.8	-	1.8	V	
High Level Output Voltage CMOS Loads	$V_{OH}$	$V_{IH}$ or $V_{IL}$	-0.02	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads	$V_{OH}$	$V_{IH}$ or $V_{IL}$	-	-	-	-	-	-	-	-	-	V	
			-6	-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	$V_{OL}$	$V_{IH}$ or $V_{IL}$	0.02	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads	$V_{OL}$	$V_{IH}$ or $V_{IL}$	-	-	-	-	-	-	-	-	-	V	
			6	6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	$I_I$	$V_{CC}$ or GND	-	6	-	-	$\pm 0.1$	-	$\pm 1$	-	$\pm 1$	$\mu A$	

**CD54HC640, CD74HC640, CD54HCT640, CD74HCT640**

**DC Electrical Specifications (Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS		V <sub>CC</sub> (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V <sub>I</sub> (V)	I <sub>O</sub> (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or GND	0	6	-	-	8	-	80	-	160	μA
Three-State Leakage Current	I <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	6	-	-	±0.5	-	±5	-	±10	μA
<b>HCT TYPES</b>												
High Level Input Voltage	V <sub>IH</sub>	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V <sub>IL</sub>	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V <sub>OH</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I <sub>I</sub>	V <sub>CC</sub> and GND	0	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or GND	0	5.5	-	-	8	-	80	-	160	μA
Three-State Leakage Current	I <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	5.5	-	-	±0.5	-	±5	-	±10	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI <sub>CC</sub> (Note 2)	V <sub>CC</sub> -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA

NOTE:

2. For dual-supply systems theoretical worst case (V<sub>I</sub> = 2.4V, V<sub>CC</sub> = 5.5V) specification is 1.8mA.

**HCT Input Loading Table**

INPUT	UNIT LOADS
DIR	0.9
$\overline{OE}$ , A	1.5
B	1.5

NOTE: Unit Load is ΔI<sub>CC</sub> limit specified in DC Electrical Table, e.g., 360μA max at 25°C.

**CD54HC640, CD74HC640, CD54HCT640, CD74HCT640**

**Switching Specifications**  $C_L = 50\text{pF}$ , Input  $t_r, t_f = 6\text{ns}$

PARAMETER	SYMBOL	TEST CONDITIONS	$V_{CC}$ (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
<b>HC TYPES</b>											
Propagation Delay A to $\bar{B}$ B to $\bar{A}$	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	2	-	-	90	-	115	-	135	ns
			4.5	-	-	18	-	23	-	27	ns
		$C_L = 15\text{pF}$	5	-	7	-	-	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	-	15	-	20	-	23	ns
Output High-Z To High Level, To Low Level	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		$C_L = 15\text{pF}$	5	-	12	-	-	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	-	26	-	33	-	38	ns
Output High Level Output Low Level to High Z	$t_{PHZ}, t_{PLZ}$	$C_L = 50\text{pF}$	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		$C_L = 15\text{pF}$	5	-	12	-	-	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	-	26	-	33	-	38	ns
Output Transition Time	$t_{THL}, t_{TLH}$	$C_L = 50\text{pF}$	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	$C_{IN}$	$C_L = 50\text{pF}$	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	$C_O$	-	-	-	20	-	20	-	20	pF	
Power Dissipation Capacitance (Notes 3, 4)	$C_{PD}$	-	5	-	38	-	-	-	-	-	pF
<b>HCT TYPES</b>											
Propagation Delay A to $\bar{B}$ B to $\bar{A}$	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	4.5	-	-	22	-	28	-	33	ns
		$C_L = 15\text{pF}$	5	-	9	-	-	-	-	-	ns
Output High-Z To High Level, To Low Level	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	4.5	-	-	30	-	38	-	45	ns
		$C_L = 15\text{pF}$	5	-	12	-	-	-	-	-	ns
Output High Level Output Low Level to High Z	$t_{PHZ}, t_{PLZ}$	$C_L = 50\text{pF}$	4.5	-	-	30	-	38	-	45	ns
		$C_L = 15\text{pF}$	5	-	12	-	-	-	-	-	ns
Output Transition Time	$t_{THL}, t_{TLH}$	$C_L = 50\text{pF}$	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	$C_{IN}$	$C_L = 50\text{pF}$	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	$C_O$	-	-	-	20	-	20	-	20	pF	
Power Dissipation Capacitance (Notes 3, 4)	$C_{PD}$	-	5	-	41	-	-	-	-	-	pF

**NOTES:**

- $C_{PD}$  is used to determine the dynamic power consumption, per channel.
- $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where  $f_i$  = Input Frequency,  $C_L$  = Output Load Capacitance,  $V_{CC}$  = Supply Voltage.

Test Circuits and Waveforms

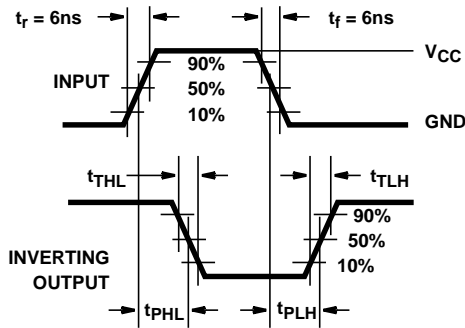


FIGURE 7. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

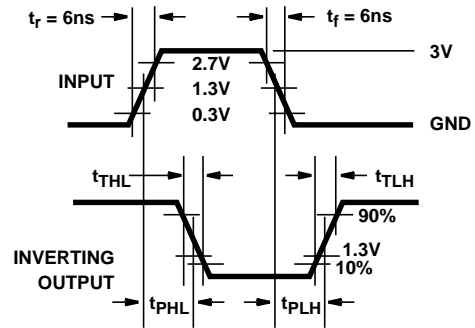


FIGURE 8. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

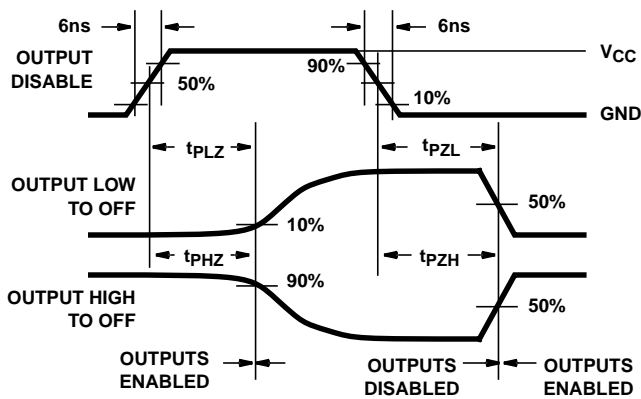


FIGURE 9. HC THREE-STATE PROPAGATION DELAY WAVEFORM

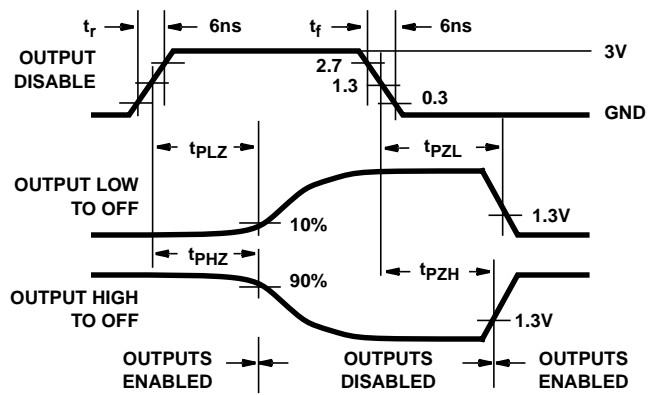
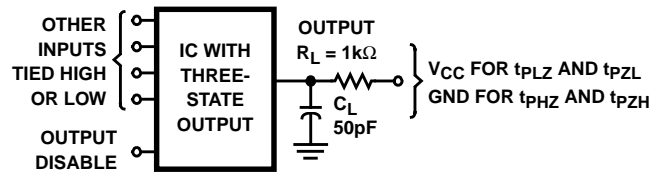


FIGURE 10. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms  $t_{PLZ}$  and  $t_{PZL}$  are the same as those for three-state shown on the left. The test circuit is Output  $R_L = 1k\Omega$   $V_{CC}$ ,  $C_L = 50pF$ .

FIGURE 11. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
5962-8974001RA	ACTIVE	CDIP	J	20	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	5962-8974001RA CD54HCT640F3A	<a href="#">Samples</a>
CD54HC640F3A	ACTIVE	CDIP	J	20	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	5962-8780901RA CD54HC640F3A	<a href="#">Samples</a>
CD54HCT640F3A	ACTIVE	CDIP	J	20	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	5962-8974001RA CD54HCT640F3A	<a href="#">Samples</a>
CD74HC640E	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC640E	<a href="#">Samples</a>
CD74HC640M	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC640M	<a href="#">Samples</a>
CD74HCT640E	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT640E	<a href="#">Samples</a>
CD74HCT640M	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT640M	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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**OTHER QUALIFIED VERSIONS OF CD54HC640, CD54HCT640, CD74HC640, CD74HCT640 :**

- Catalog: [CD74HC640](#), [CD74HCT640](#)
- Military: [CD54HC640](#), [CD54HCT640](#)

NOTE: Qualified Version Definitions:

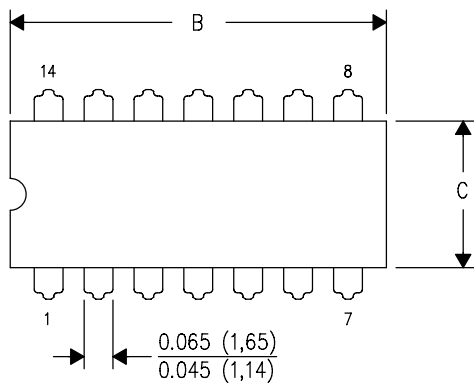
- Catalog - TI's standard catalog product
- Military - QML certified for Military and Defense Applications



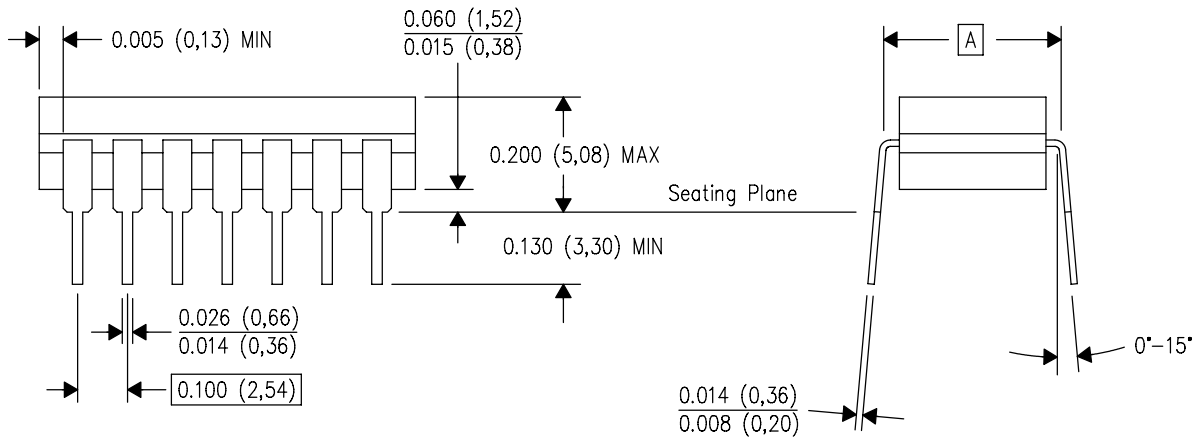
J (R-GDIP-T\*\*)

14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE



DIM \ PINS **	14	16	18	20
A	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC
B MAX	0.785 (19,94)	.840 (21,34)	0.960 (24,38)	1.060 (26,92)
B MIN	—	—	—	—
C MAX	0.300 (7,62)	0.300 (7,62)	0.310 (7,87)	0.300 (7,62)
C MIN	0.245 (6,22)	0.245 (6,22)	0.220 (5,59)	0.245 (6,22)



4040083/F 03/03

- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - C. This package is hermetically sealed with a ceramic lid using glass frit.
  - D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
  - E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - C Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
  - D The 20 pin end lead shoulder width is a vendor option, either half or full width.

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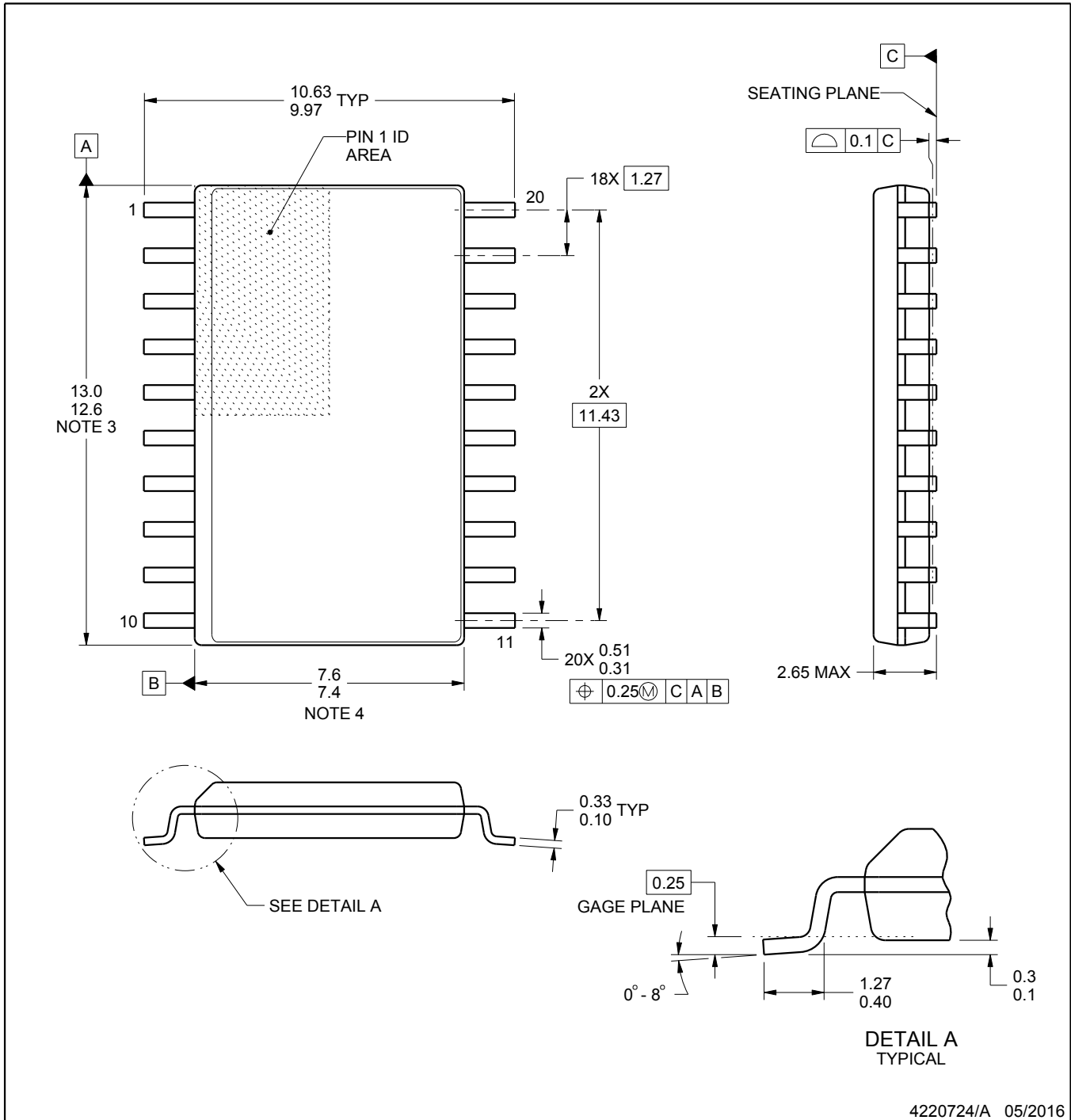
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# PACKAGE OUTLINE

## SOIC - 2.65 mm max height

SOIC



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**NOTES:**

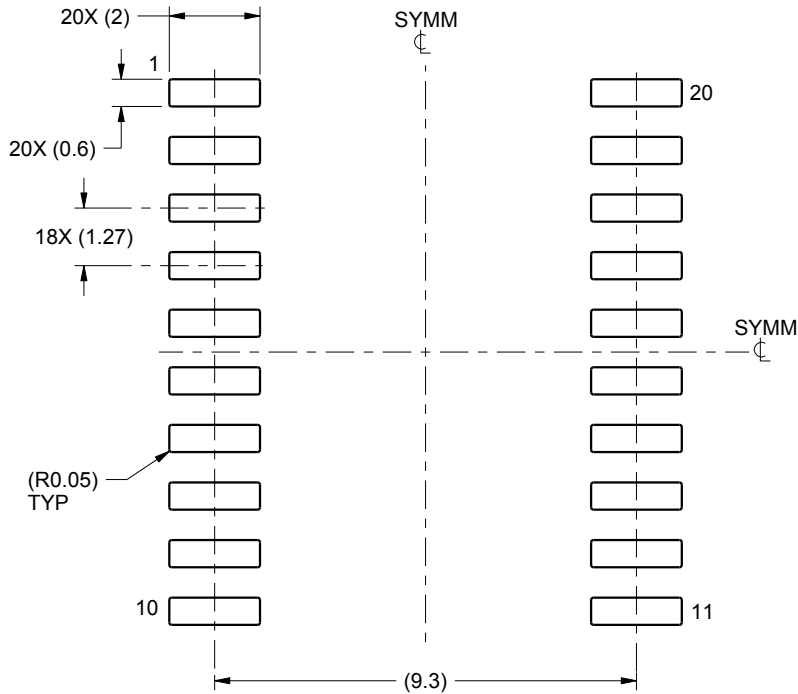
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.

# EXAMPLE BOARD LAYOUT

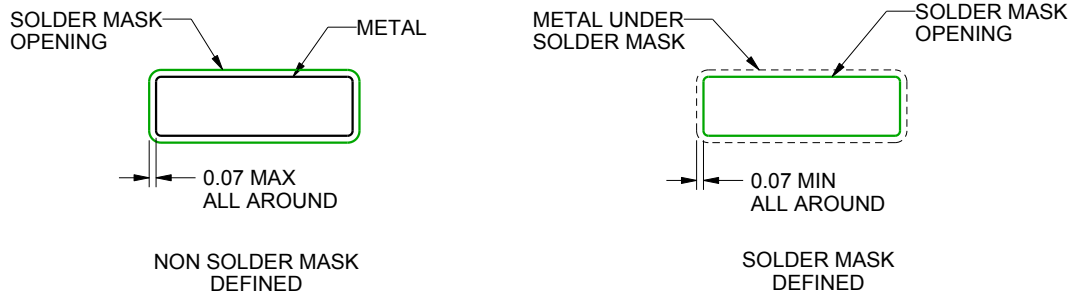
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SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE  
SCALE:6X



SOLDER MASK DETAILS

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NOTES: (continued)

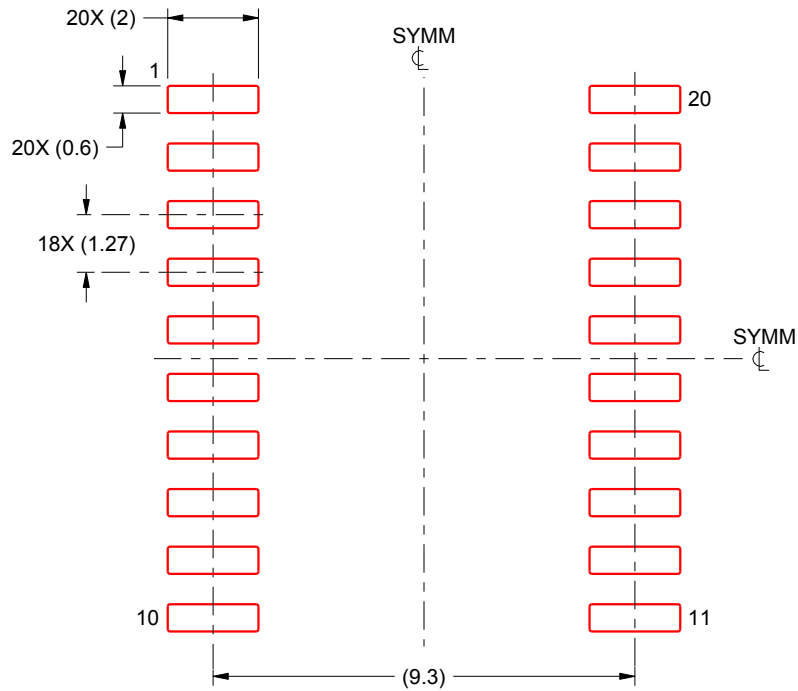
- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DW0020A

SOIC - 2.65 mm max height

SOIC



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:6X

4220724/A 05/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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